



# 1N5221B - 1N5279B

## Zeners

### Absolute Maximum Ratings\* T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
P <sub>D</sub>	Power Dissipation Derate above 50°C	500	mW
		4.0	mW/°C
T <sub>STG</sub>	Storage Temperature Range	-65 to +200	°C
T <sub>J</sub>	Maximum Junction Operating Temperature	+200	°C
	Lead Temperature (1/16" from case for 10 seconds)	+230	°C

Tolerance = 5%



\* These ratings are limiting values above which the serviceability of the diode may be impaired.

\*\* Non-recurrent square wave PW = 8.3ms, T<sub>a</sub> = 50 degrees C.

### Electrical Characteristics T<sub>A</sub>=25°C unless otherwise noted

Device	V <sub>Z</sub> (V) @ I <sub>Z</sub> (Note 1)			Z <sub>Z</sub> (Ω) @ I <sub>Z</sub> (mA)		Z <sub>ZK</sub> (Ω) @ I <sub>ZK</sub> (mA)		I <sub>R</sub> (μA) @ V <sub>R</sub> (V)		T <sub>C</sub> (%/°C)
	Min.	Typ.	Max.							
1N5221B	2.28	2.4	2.52	30	20	1,200	0.25	100	1.0	-0.085
1N5222B	2.375	2.5	2.625	30	20	1,250	0.25	100	1.0	-0.085
1N5223B	2.565	2.7	2.835	30	20	1,300	0.25	75	1.0	-0.080
1N5224B	2.66	2.8	2.94	30	20	1,400	0.25	75	1.0	-0.080
1N5225B	2.85	3	3.15	29	20	1,600	0.25	50	1.0	-0.075
1N5226B	3.135	3.3	3.465	28	20	1,600	0.25	25	1.0	-0.07
1N5227B	3.42	3.6	3.78	24	20	1,700	0.25	15	1.0	-0.065
1N5228B	3.705	3.9	4.095	23	20	1,900	0.25	10	1.0	-0.06
1N5229B	4.085	4.3	4.515	22	20	2,000	0.25	5.0	1.0	+/-0.055
1N5230B	4.465	4.7	4.935	19	20	1,900	0.25	2.0	1.0	+/-0.03
1N5231B	4.845	5.1	5.355	17	20	1,600	0.25	5.0	2.0	+/-0.03
1N5232B	5.32	5.6	5.88	11	20	1,600	0.25	5.0	3.0	0.038
1N5233B	5.7	6	6.3	7.0	20	1,600	0.25	5.0	3.5	0.038
1N5234B	5.89	6.2	6.51	7.0	20	1,000	0.25	5.0	4.0	0.045
1N5235B	6.46	6.8	7.14	5.0	20	750	0.25	3.0	5.0	0.05
1N5236B	7.125	7.5	7.875	6.0	20	500	0.25	3.0	6.0	0.058
1N5237B	7.79	8.2	8.61	8.0	20	500	0.25	3.0	6.5	0.062
1N5238B	8.265	8.7	9.135	8.0	20	600	0.25	3.0	6.5	0.065
1N5239B	8.645	9.1	9.555	10	20	600	0.25	3.0	7.0	0.068
1N5240B	9.5	10	10.5	17	20	600	0.25	3.0	8.0	0.075
1N5241B	10.45	11	11.55	22	20	600	0.25	2.0	8.4	0.076
1N5242B	11.4	12	12.6	30	20	600	0.25	0.1	9.1	0.077
1N5243B	12.35	13	13.65	13	9.5	600	0.25	0.1	9.9	0.079
1N5244B	13.3	14	14.7	15	9.0	600	0.25	0.1	10	0.080
1N5245B	14.25	15	15.75	16	8.5	600	0.25	0.1	11	0.082
1N5246B	15.2	16	16.8	17	7.8	600	0.25	0.1	12	0.083
1N5247B	16.15	17	17.85	19	7.4	600	0.25	0.1	13	0.084
1N5248B	17.1	18	18.9	21	7.0	600	0.25	0.1	14	0.085
1N5249B	18.05	19	19.95	23	6.6	600	0.25	0.1	14	0.085
1N5250B	19	20	21	25	6.2	600	0.25	0.1	15	0.086

**Electrical Characteristics** (Continued)  $T_A=25^\circ\text{C}$  unless otherwise noted

Device	$V_Z$ (V) @ $I_Z$ (Note 1)			$Z_Z$ ( $\Omega$ ) @ $I_Z$ (mA)		$Z_{ZK}$ ( $\Omega$ ) @ $I_{ZK}$ (mA)		$I_R$ ( $\mu\text{A}$ ) @ $V_R$ (V)		$T_C$ (%/ $^\circ\text{C}$ )
	Min.	Typ.	Max.							
1N5251B	20.9	22	23.1	29	5.6	600	0.25	0.1	17	0.087
1N5252B	22.8	24	25.2	33	5.2	600	0.25	0.1	18	0.088
1N5253B	23.75	25	26.25	35	5.0	600	0.25	0.1	19	0.088
1N5254B	25.65	27	28.35	41	4.6	600	0.25	0.1	21	0.089
1N5255B	26.6	28	29.4	44	4.5	600	0.25	0.1	21	0.090
1N5256B	28.5	30	31.5	49	4.2	600	0.25	0.1	23	0.09
1N5257B	31.35	33	34.65	58	3.8	700	0.25	0.1	25	0.092
1N5258B	34.2	36	37.8	70	3.4	700	0.25	0.1	27	0.093
1N5259B	37.05	39	40.95	80	3.2	800	0.25	0.1	30	0.094
1N5260B	40.85	43	45.15	93	3.0	900	0.25	0.1	33	0.095
1N5261B	44.65	47	49.35	105	2.7	1000	0.25	0.1	36	0.095
1N5262B	48.45	51	53.55	125	2.5	1100	0.25	0.1	39	0.096
1N5263B	53.2	56	58.8	150	2.2	1300	0.25	0.1	43	0.096
1N5264B	57	60	63	170	2.1	1400	0.25	0.1	46	0.097
1N5265B	58.9	62	65.1	185	2.0	1400	0.25	0.1	47	0.097
1N5266B	64.6	68	71.4	230	1.8	1600	0.25	0.1	52	0.097
1N5267B	71.25	75	78.75	270	1.7	1700	0.25	0.1	56	0.098
1N5268B	80.75	85	89.25	330	1.5	2000	0.25	0.1	62	0.098
1N5269B	82.65	87	91.35	370	1.4	2200	0.25	0.1	68	0.099
1N5270B	96.45	91	95.55	400	1.4	2300	0.25	0.1	69	0.099
1N5271B	95	100	105	500	1.3	2600	0.25	0.1	76	0.099
1N5272B	104.5	110	115.5	750	1.1	3000	0.25	0.1	84	0.11
1N5273B	114	120	126	900	1.0	4000	0.25	0.1	91	0.11
1N5274B	123.5	130	136.5	1100	0.95	4500	0.25	0.1	99	0.11
1N5275B	133	140	147	1300	0.90	4500	0.25	0.1	106	0.11
1N5276B	142.5	150	157.5	1500	0.85	5000	0.25	0.1	114	0.11
1N5277B	152	160	168	1700	0.80	5500	0.25	0.1	122	0.11
1N5278B	161.5	170	178.5	1900	0.74	5500	0.25	0.1	129	0.11
1N5279B	171	180	189	2200	0.68	6000	0.25	0.1	137	0.11

 **$V_F$  Forward Voltage = 1.2V Max. @  $I_F = 200\text{mA}$** **Notes:**- Zener Voltage ( $V_Z$ ) : The zener voltage is measured with the device junction in the thermal equilibrium at the lead temperature ( $T_L$ ) at  $30^\circ\text{C} \pm 1^\circ\text{C}$  and 3/8" lead length.

## Top Mark Information

Device	Line 1	Line 2	Line 3
1N5221B	LOGO	22	1B
1N5222B	LOGO	22	2B
1N5223B	LOGO	22	3B
1N5224B	LOGO	22	4B
1N5225B	LOGO	22	5B
1N5226B	LOGO	22	6B
1N5227B	LOGO	22	7B
1N5228B	LOGO	22	8B
1N5229B	LOGO	22	9B
1N5230B	LOGO	23	0B
1N5231B	LOGO	23	1B
1N5232B	LOGO	23	2B
1N5233B	LOGO	23	3B
1N5234B	LOGO	23	4B
1N5235B	LOGO	23	5B
1N5236B	LOGO	23	6B
1N5237B	LOGO	23	7B
1N5238B	LOGO	23	8B
1N5239B	LOGO	23	9B
1N5240B	LOGO	24	0B
1N5241B	LOGO	24	1B
1N5242B	LOGO	24	2B
1N5243B	LOGO	24	3B
1N5244B	LOGO	24	4B
1N5245B	LOGO	24	5B
1N5246B	LOGO	24	6B
1N5247B	LOGO	24	7B
1N5248B	LOGO	24	8B
1N5247B	LOGO	24	9B
1N5250B	LOGO	25	0B
1N5251B	LOGO	25	1B
1N5252B	LOGO	25	2B
1N5253B	LOGO	25	3B
1N5254B	LOGO	25	4B
1N5255B	LOGO	25	5B
1N5256B	LOGO	25	6B
1N5257B	LOGO	25	7B
1N5258B	LOGO	25	8B
1N5259B	LOGO	25	9B
1N5260B	LOGO	26	0B
1N5261B	LOGO	26	1B
1N5262B	LOGO	26	2B
1N5263B	LOGO	26	3B
1N5264B	LOGO	26	4B
1N5265B	LOGO	26	5B
1N5266B	LOGO	26	6B
1N5267B	LOGO	26	7B
1N5268B	LOGO	26	8B
1N5269B	LOGO	26	9B
1N5270B	LOGO	26	0B
1N5271B	LOGO	27	1B
1N5272B	LOGO	27	2B
1N5273B	LOGO	27	3B
1N5274B	LOGO	27	4B
1N5275B	LOGO	27	5B
1N5276B	LOGO	27	6B
1N5277B	LOGO	27	7B
1N5278B	LOGO	27	8B
1N5279B	LOGO	27	9B

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